

DATA SHEET

PUMX1 Dual NPN transistor

Preliminary specification
File under Discrete Semiconductors, SC04

1995 Dec 07

Dual NPN transistor

PUMX1

FEATURES

- Two transistors in one SC70 package
- Reduces number of components and boardspace
- No mutual interference between the transistors.

PINNING

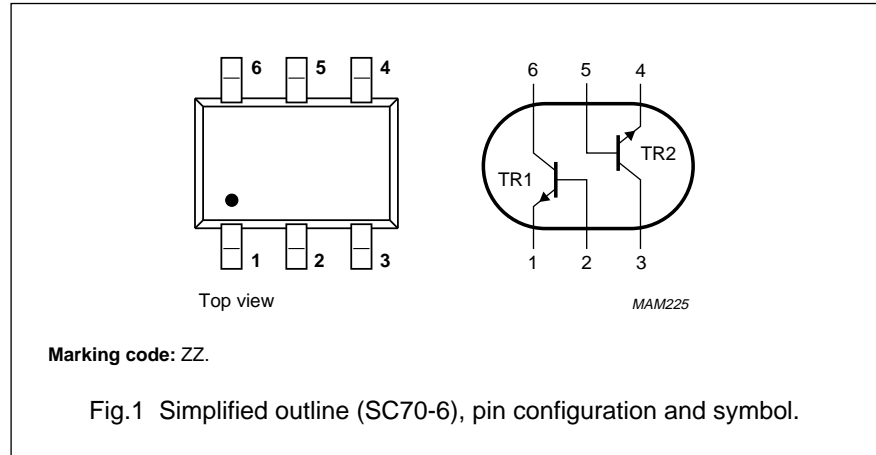
PIN	DESCRIPTION
1	emitter TR1
2	base TR1
3	collector TR2
4	emitter TR2
5	base TR2
6	collector TR1

APPLICATIONS

- General purpose switching
- Small signal amplification.

DESCRIPTION

Two NPN transistors in a plastic six lead SC70-6 (S-mini) package.



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
V_{CBO}	collector-base voltage	open emitter	–	50	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	100	mA
h_{FE}	DC current gain	$I_C = 1 \text{ mA}; V_{CE} = 6 \text{ V}$	120	–	
f_T	transition frequency	$I_C = 2 \text{ mA}; V_{CE} = 12 \text{ V}; f = 100 \text{ MHz}; T_{amb} = 25 \text{ }^\circ\text{C}$	100	–	MHz
Per package					
P_{tot}	total power dissipation	up to $T_{amb} = 25 \text{ }^\circ\text{C}$	–	300	mW

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
V_{CBO}	collector-base voltage	open emitter	–	50	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	100	mA
P_{tot}	total power dissipation		–	200	mW
T_{amb}	operating ambient temperature		–65	+150	°C
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
Per package					
P_{tot}	total power dissipation	up to $T_{amb} = 25\text{ °C}$; note 1	–	300	mW

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	416	K/W

Note to the ‘Limiting values’ and ‘Thermal characteristics’

- In accordance with standard mounting conditions SC70, six lead version.

ELECTRICAL CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = 50\ \mu\text{A}$; $I_E = 0$	50	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; $I_C = 1\ \text{mA}$; $I_B = 0$	40	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; $I_E = 50\ \mu\text{A}$; $I_C = 0$	5	–	V
V_{CEsat}	collector-emitter saturation voltage	$I_C = 50\ \text{mA}$; $I_B = 5\ \text{mA}$; note 1	–	200	mV
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\ \text{V}$; $I_E = 0$	–	100	nA
		$V_{CB} = 30\ \text{V}$; $I_E = 0$; $T_j = 150\text{ °C}$	–	10	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 4\ \text{V}$; $I_C = 0$	–	100	nA
h_{FE}	DC current gain	$I_C = 1\ \text{mA}$; $V_{CE} = 6\ \text{V}$	120	–	
f_T	transition frequency	$I_C = 2\ \text{mA}$; $V_{CE} = 12\ \text{V}$; $f = 100\ \text{MHz}$	100	–	MHz
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 12\ \text{V}$; $f = 1\ \text{MHz}$	–	2.2	pF

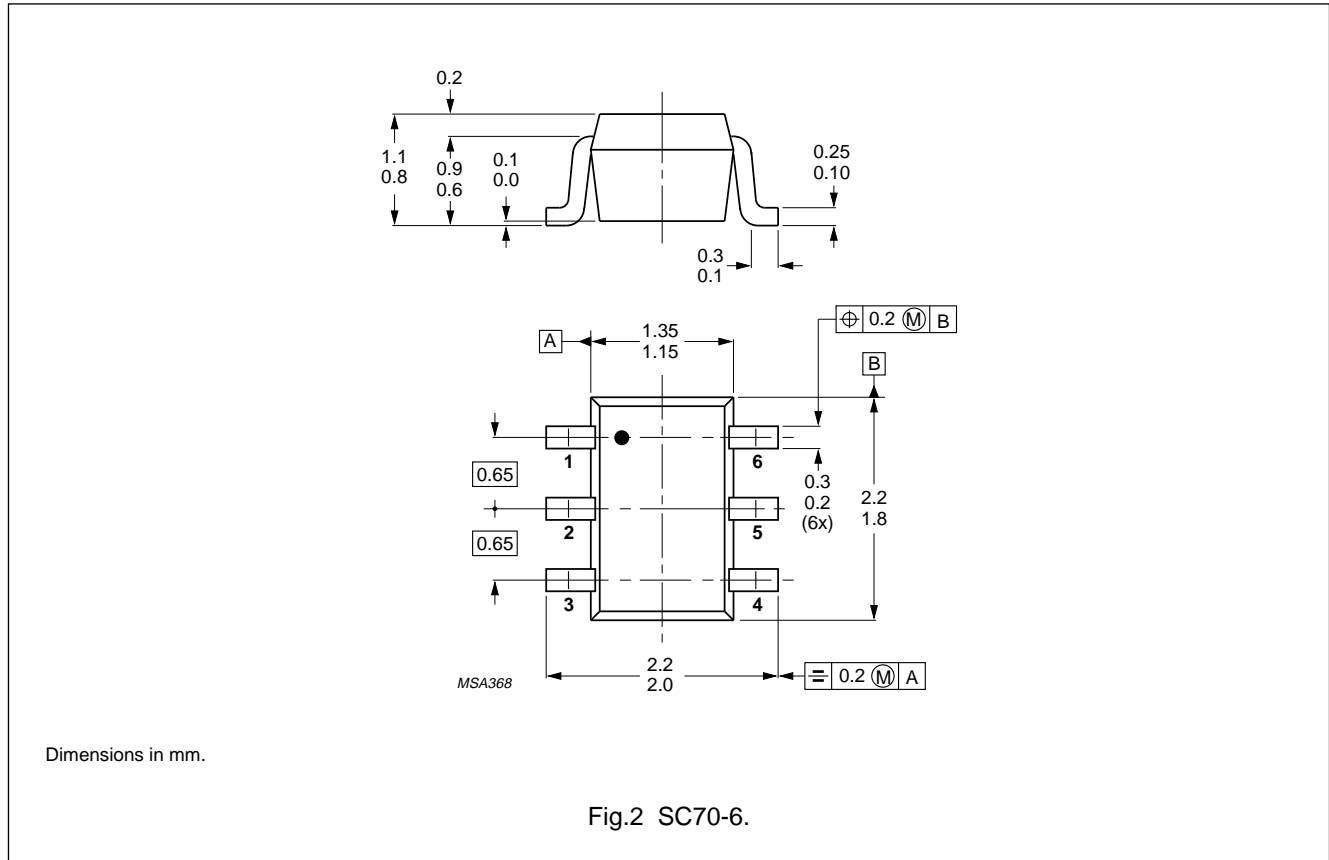
Note to the ‘Electrical characteristics’

- Pulse test: $t_p \leq 300\ \mu\text{s}$; $\delta \leq 0.02$.

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PACKAGE OUTLINE



DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Philips Semiconductors – a worldwide company

Argentina: IEROD, Av. Juramento 1992 - 14.b, (1428)
BUENOS AIRES, Tel. (541)786 7633, Fax. (541)786 9367

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. (02)805 4455, Fax. (02)805 4466

Austria: Triester Str. 64, A-1101 WIEN, P.O. Box 213,
Tel. (01)60 101-1236, Fax. (01)60 101-1211

Belgium: Postbus 90050, 5600 PB EINDHOVEN, The Netherlands,
Tel. (31)40-2783749, Fax. (31)40-2788399

Brazil: Rua do Rocio 220 - 5th floor, Suite 51,
CEP: 04552-903-SÃO PAULO-SP, Brazil,
P.O. Box 7383 (01064-970),
Tel. (011)821-2333, Fax. (011)829-1849

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS:
Tel. (800) 234-7381, Fax. (708) 296-8556

Chile: Av. Santa Maria 0760, SANTIAGO,
Tel. (02)773 816, Fax. (02)777 6730

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. (852)2319 7888, Fax. (852)2319 7700

Colombia: IPRELENZO LTDA, Carrera 21 No. 56-17,
77621 BOGOTA, Tel. (571)249 7624/(571)217 4609,
Fax. (571)217 4549

Denmark: Prags Boulevard 80, PB 1919, DK-2300
COPENHAGEN S, Tel. (45)32 88 26 36, Fax. (45)31 57 19 49

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. (358)0-615 800, Fax. (358)0-61580 920

France: 4 Rue du Port-aux-Vins, BP317,
92156 SURESNES Cedex,
Tel. (01)4099 6161, Fax. (01)4099 6427

Germany: P.O. Box 10 51 40, 20035 HAMBURG,
Tel. (040)23 53 60, Fax. (040)23 53 63 00

Greece: No. 15, 25th March Street, GR 17778 TAVROS,
Tel. (01)4894 339/4894 911, Fax. (01)4814 240

India: Philips INDIA Ltd, Shivsagar Estate, A Block,
Dr. Annie Besant Rd. Worli, Bombay 400 018
Tel. (022)4938 541, Fax. (022)4938 722

Indonesia: Philips House, Jalan H.R. Rasuna Said Kav. 3-4,
P.O. Box 4252, JAKARTA 12950,
Tel. (021)5201 122, Fax. (021)5205 189

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. (01)7640 000, Fax. (01)7640 200

Italy: PHILIPS SEMICONDUCTORS S.r.l.,
Piazza IV Novembre 3, 20124 MILANO,
Tel. (0039)2 6752 2531, Fax. (0039)2 6752 2557

Japan: Philips Bldg 13-37, Kohnan2-chome, Minato-ku, TOKYO 108,
Tel. (03)3740 5130, Fax. (03)3740 5077

Korea: Philips House, 260-199 Itaewon-dong,
Yongsan-ku, SEOUL, Tel. (02)709-1412, Fax. (02)709-1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA,
SELANGOR, Tel. (03)750 5214, Fax. (03)757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TX 79905,
Tel. 9-5(800)234-7381, Fax. (708)296-8556

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. (040)2783749, Fax. (040)2788399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. (09)849-4160, Fax. (09)849-7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. (022)74 8000, Fax. (022)74 8341

Pakistan: Philips Electrical Industries of Pakistan Ltd.,
Exchange Bldg. ST-2/A, Block 9, KDA Scheme 5, Clifton,
KARACHI 75600, Tel. (021)587 4641-49,
Fax. (021)577035/5874546

Philippines: PHILIPS SEMICONDUCTORS PHILIPPINES Inc.,
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Metro MANILA, Tel. (63) 2 816 6380, Fax. (63) 2 817 3474

Portugal: PHILIPS PORTUGUESA, S.A.,
Rua dr. António Loureiro Borges 5, Arquiparque - Miraflores,
Apartado 300, 2795 LINDA-A-VELHA,
Tel. (01)4163160/4163333, Fax. (01)4163174/4163366

Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231,
Tel. (65)350 2000, Fax. (65)251 6500

South Africa: S.A. PHILIPS Pty Ltd.,
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Tel. (011)470-5911, Fax. (011)470-5494

Spain: Balmes 22, 08007 BARCELONA,
Tel. (03)301 6312, Fax. (03)301 42 43

Sweden: Kottbygatan 7, Akalla. S-164 85 STOCKHOLM,
Tel. (08)632 2000, Fax. (08)632 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
Tel. (01)488 2211, Fax. (01)481 77 30

Taiwan: PHILIPS TAIWAN Ltd., 23-30F, 66, Chung Hsiao West
Road, Sec. 1. Taipei, Taiwan ROC, P.O. Box 22978,
TAIPEI 100, Tel. (886) 2 382 4443, Fax. (886) 2 382 4444

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
209/2 Sanpavuth-Bangna Road Prakanong,
Bangkok 10260, THAILAND,
Tel. (66) 2 745-4090, Fax. (66) 2 398-0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,
Tel. (0212)279 27 70, Fax. (0212)282 67 07

Ukraine: Philips UKRAINE, 2A Akademika Koroleva str., Office 165,
252148 KIEV, Tel. 380-44-4760297, Fax. 380-44-4766991

United Kingdom: Philips Semiconductors LTD.,
276 Bath Road, Hayes, MIDDLESEX UB3 5BX,
Tel. (0181)730-5000, Fax. (0181)754-8421

United States: 811 East Arques Avenue, SUNNYVALE,
CA 94088-3409, Tel. (800)234-7381, Fax. (708)296-8556

Uruguay: Coronel Mora 433, MONTEVIDEO,
Tel. (02)70-4044, Fax. (02)92 0601

Internet: <http://www.semiconductors.philips.com/ps/>

For all other countries apply to: Philips Semiconductors,
International Marketing and Sales, Building BE-p,
P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands,
Telex 35000 phtcnl, Fax. +31-40-2724825

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Printed in The Netherlands

113062/1100/01/pp8

Document order number:

Date of release: 1995 Dec 07

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